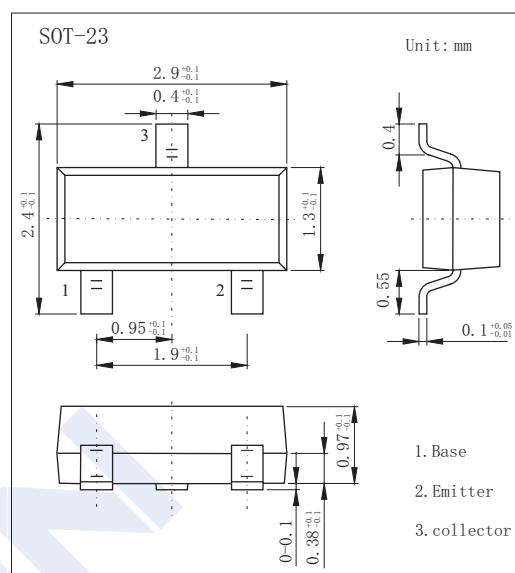


PNP Transistor

STR2550

■ Features

- Excellent h_{FE} linearity up to 50 mA
- The NPN complementary type is STR1550

■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}.$)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-500	V
Collector - Emitter Voltage	V_{CE0}	-500	
Emitter - Base Voltage	V_{EB0}	-7	
Collector Current (DC)	I_C	-0.5	A
Collector peak current ($t_p < 5$ ms)	I_{CM}	-1	
Power Dissipation	P_C	500	mW
Thermal Resistance Junction to Ambient ^{*1}	$R_{\theta JA}$	250	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to +150	

*1. Device mounted on PCB area of 1 cm².

PNP Transistor

STR2550

■ Electrical Characteristics (T_c = 25 °C unless otherwise specified.)

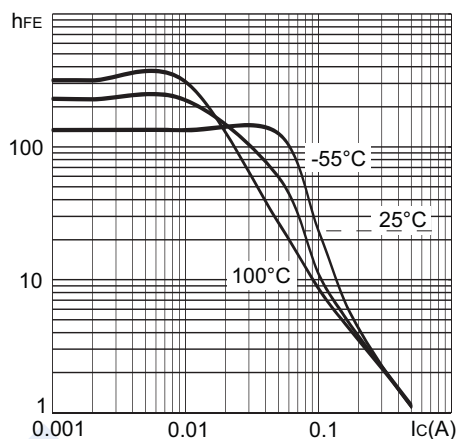
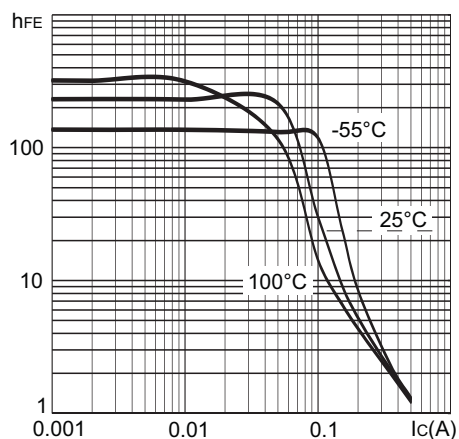
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = -100 μA , I _E = 0	-500			V
Collector- emitter breakdown voltage ^{*1}	V _{CE0}	I _c = -1 mA , I _B = 0	-500			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA , I _c = 0	-7			
Collector-base cut-off current	I _{CB0}	V _{CB} = -500V , I _E = 0			-10	μA
Emitter cut-off current	I _{EB0}	V _{EB} = -5V , I _c = 0			-1	
Collector-emitter saturation voltage ^{*1}	V _{CE(sat)}	I _c = -20mA , I _B = -2mA			-0.2	V
		I _c = -50mA , I _B = -10mA			-0.3	
Base - emitter saturation voltage ^{*1}	V _{BE(sat)}	I _c = -50mA , I _B = -10mA			-1.0	
Base-emitter on voltage	V _{BE(on)}	I _c = -50 mA , V _{CE} = -10 V			-1.1	
DC current gain ^{*1}	h _{FE}	V _{CE} = -10 V , I _c = -1 mA	100			
		V _{CE} = -10 V , I _c = -50 mA	100		300	
		V _{CE} = -10 V , I _c = -100 mA	10			

*1.Pulse test: pulse duration ≤ 300 μs, duty cycle ≤ 2%

■ Marking

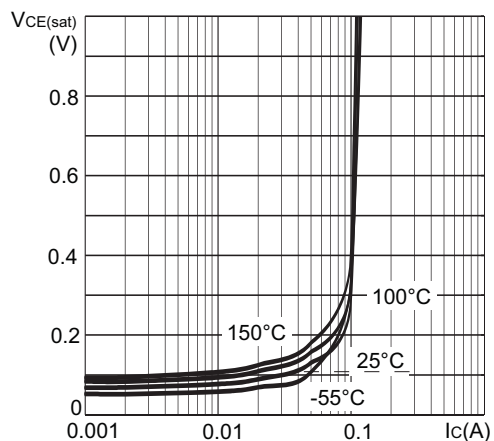
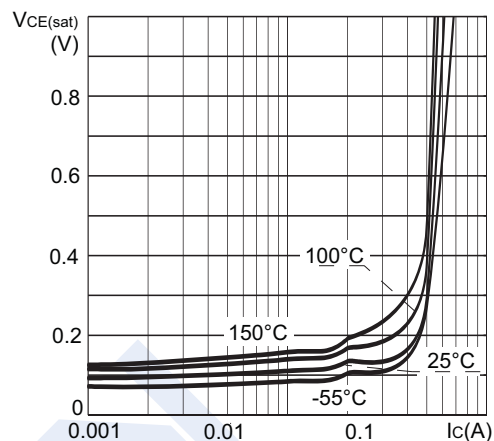
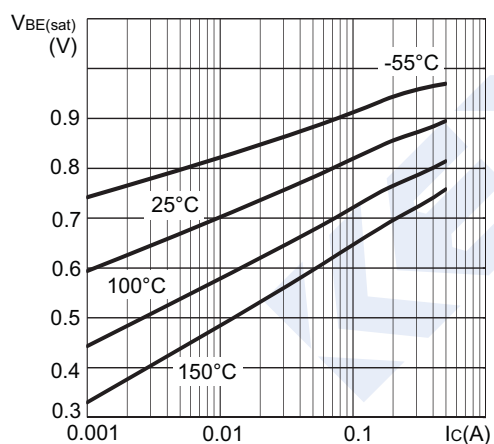
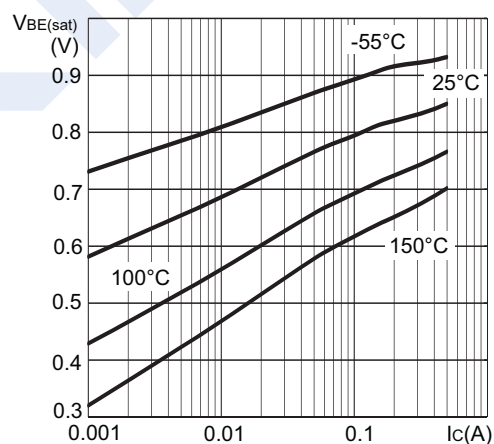
Marking	2550
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■ Typical Characteristics

Figure 1. h_{FE} vs. I_C @ V_{CE} = 5 VFigure 2. h_{FE} vs. I_C @ V_{CE} = 10 V

PNP Transistor

STR2550

Figure 3. $V_{CE(sat)}$ vs. I_C @ $h_{FE}=5$ Figure 4. $V_{CE(sat)}$ vs. I_C @ $h_{FE}=10$ Figure 5. $V_{BE(sat)}$ vs. I_C @ $h_{FE}=5$ Figure 6. $V_{BE(sat)}$ vs. I_C @ $h_{FE}=10$ Figure 7. $V_{BE(on)}$ vs. I_C @ $V_{CE}=10$ V